L Number	Hits	Search Text	DB	Time stamp
1	13354	substrate with sapphire	USPAT;	2004/06/18 09:03
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
2	654	(substrate with sapphire) and (group adj III adj nitride)	USPAT;	2004/06/18 09:03
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
3	139	((substrate with sapphire) and (group adj III adj nitride)) and ((group adj	USPAT;	2004/06/18 09:28
		III adj nitride) with (mocvd or sputter\$4 or evaporat\$4 or (ion adj	US-PGPUB;	
		plat\$4) or (laser adj ablat\$4) or ecr))	ЕРО; ЛРО;	
			DERWENT;	
4	49	(((cubetrate with combine) and (aroun edi III edi nitride)) and ((aroun	IBM_TDB	2004/06/19 00:22
4	49	(((substrate with sapphire) and (group adj III adj nitride)) and ((group adj III adj nitride) with (mocvd or sputter\$4 or evaporat\$4 or (ion adj	USPAT; US-PGPUB;	2004/06/18 09:22
		plat\$4) or (laser adj ablat\$4) or ecr))) and temperature\$2 and (flow adj	EPO; JPO;	
		rate\$2)	DERWENT;	
			IBM_TDB	
5	60	(((substrate with sapphire) and (group adj III adj nitride)) and ((group	USPAT;	2004/06/18 09:23
	00	adj III adj nitride) with (mocvd or sputter\$4 or evaporat\$4 or (ion adj	US-PGPUB;	2004/00/18 03.23
		plat\$4) or (laser adj ablat\$4) or ecr))) and (aln same sputter\$4)	EPO; JPO;	
		place i) of (label and ablace i) of body) and (and battle opation)	DERWENT;	
			IBM_TDB	
6	65	((substrate with sapphire) and (group adj III adj nitride)) and ((group adj	USPAT;	2004/06/18 09:33
		III adj nitride) with (sputter\$4 or evaporat\$4 or (ion adj plat\$4) or (laser	US-PGPUB;	
		adj ablat\$4) or ecr))	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
7	18	(((substrate with sapphire) and (group adj III adj nitride)) and ((group	USPAT;	2004/06/18 09:28
		adj III adj nitride) with (sputter\$4 or evaporat\$4 or (ion adj plat\$4) or	US-PGPUB;	
		(laser adj ablat\$4) or ecr))) not ((((substrate with sapphire) and (group	ЕРО; ЈРО;	
j		adj III adj nitride)) and ((group adj III adj nitride) with (mocvd or	DERWENT;	
		sputter\$4 or evaporat\$4 or (ion adj plat\$4) or (laser adj ablat\$4) or	IBM_TDB	
	_	ecr))) and (aln same sputter\$4))		
8	64	(((substrate with sapphire) and (group adj III adj nitride)) and ((group	USPAT;	2004/06/18 09:33
		adj III adj nitride) with (sputter\$4 or evaporat\$4 or (ion adj plat\$4) or	US-PGPUB;	
]		(laser adj ablat\$4) or ecr))) and ((group adj III adj nitride) with (method	ЕРО; ЈРО;	
		or process))	DERWENT;	
			IBM_TDB	